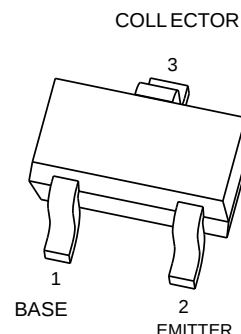




2SC5066 VHF~UHF Band Low Noise Amplifier Applications

- Low noise figure, high gain.
- $NF = 1.1\text{dB}$, $|S_{21e}|^2 = 12\text{dB}$ ($f = 1\text{GHz}$)

Marking : 2SC5066O M1
2SC5066Y M2



Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CB0}	20	V
Collector-emitter voltage	V_{CE0}	12	V
Emitter-base voltage	V_{EB0}	3	V
Base current	I_B	15	mA
Collector current	I_C	30	mA
Collector power dissipation	P_C	100	mW
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55 to 125	$^\circ\text{C}$

SOT-523

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Microwave Characteristics ($T_a = 25^\circ\text{C}$)

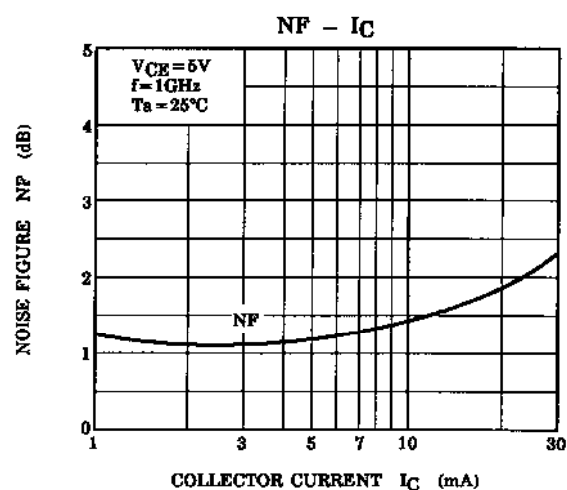
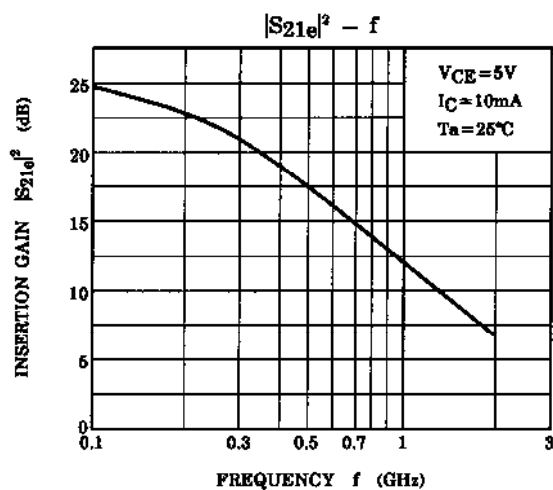
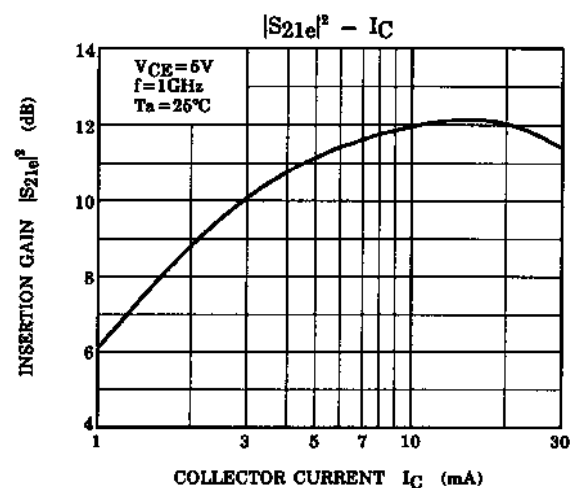
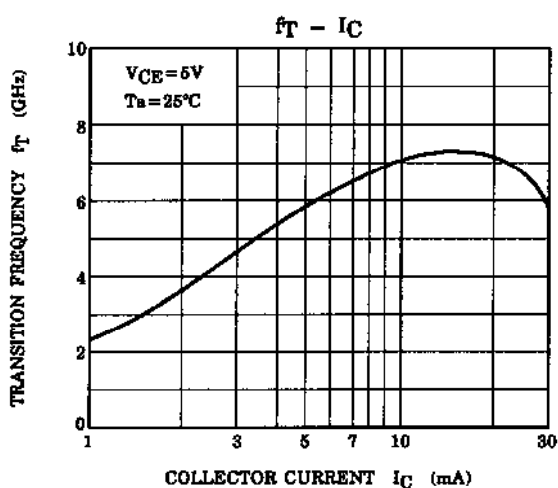
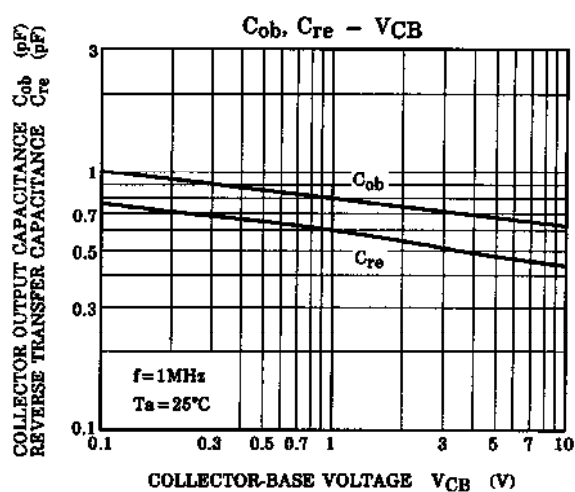
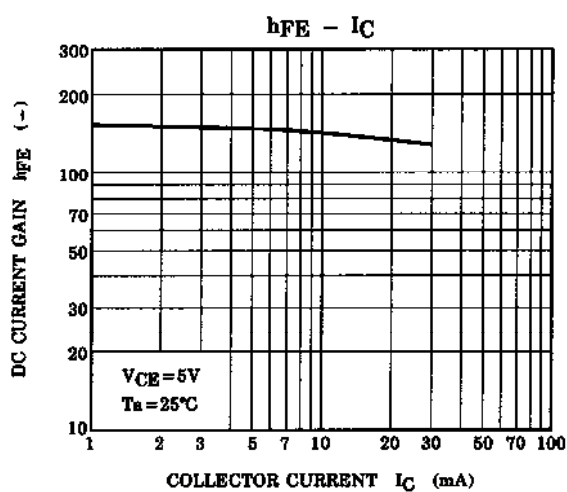
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Transition frequency	f_T	$V_{CE} = 5\text{V}$, $I_C = 10\text{mA}$	5	7	—	GHz
Insertion gain	$ S_{21e} ^2 (1)$	$V_{CE} = 5\text{V}$, $I_C = 10\text{mA}$, $f = 500\text{MHz}$	—	17	—	dB
	$ S_{21e} ^2 (2)$	$V_{CE} = 5\text{V}$, $I_C = 10\text{mA}$, $f = 1\text{GHz}$	8.5	12	—	
Noise figure	NF (1)	$V_{CE} = 5\text{V}$, $I_C = 3\text{mA}$, $f = 500\text{MHz}$	—	1	—	dB
	NF (2)	$V_{CE} = 5\text{V}$, $I_C = 3\text{mA}$, $f = 1\text{GHz}$	—	1.1	2.0	

Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = 10\text{V}$, $I_E = 0$	—	—	1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 1\text{V}$, $I_C = 0$	—	—	1	μA
DC current gain	h_{FE} (Note 1)	$V_{CE} = 5\text{V}$, $I_C = 10\text{mA}$	80	—	160	
Output capacitance	C_{ob}	$V_{CB} = 5\text{V}$, $I_E = 0$, $f = 1\text{MHz}$ (Note 2)	—	0.7	—	
Reverse transfer capacitance	C_{re}		—	0.45	0.9	pF

Note 1: h_{FE} classification O: 80 to 160, Y: 120 to 240

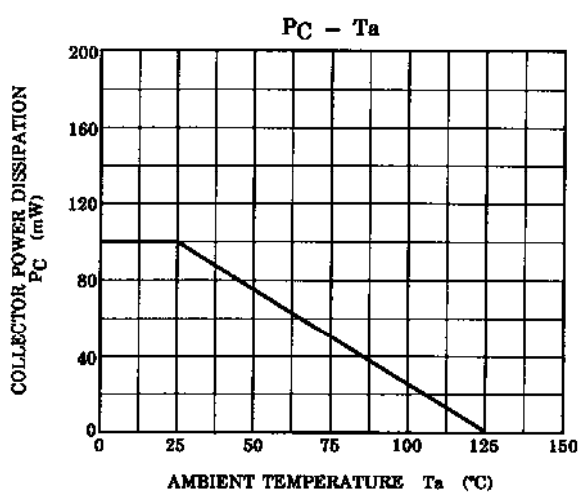
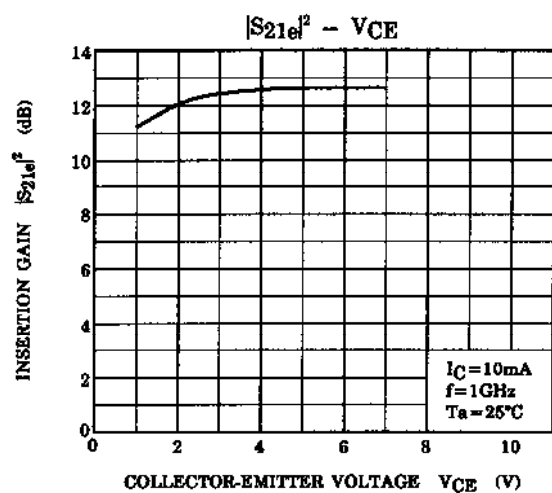
Note 2: C_{re} is measured by 3 terminal method with capacitance bridge.





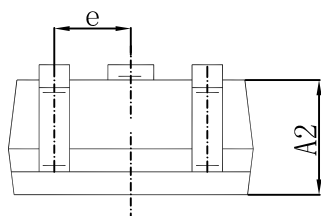
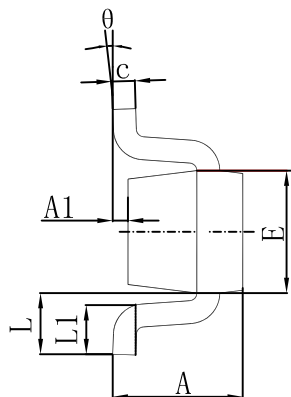
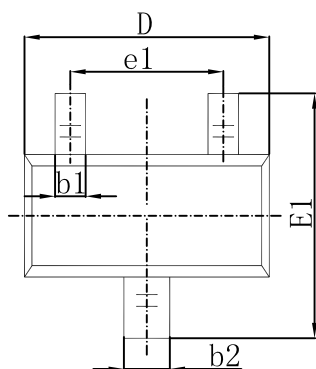
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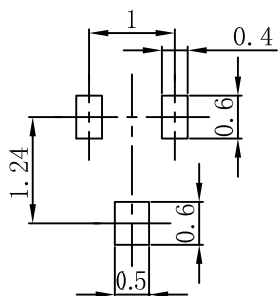


SOT-523 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.250	0.350	0.010	0.014
c	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.700	0.900	0.028	0.035
E1	1.450	1.750	0.057	0.069
e	0.500 TYP.		0.020 TYP.	
e1	0.900	1.100	0.035	0.043
L	0.400 REF.		0.016 REF.	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

SOT-523 Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.